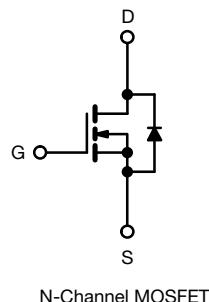
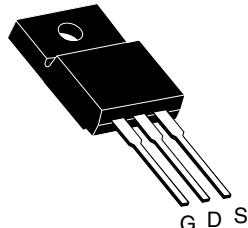


E Series Power MOSFET

TO-220 FULLPAK


FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V	0.070
Q_g max. (nC)	63	
Q_{gs} (nC)	19	
Q_{gd} (nC)	10	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free and halogen-free	SIHF080N60E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	± 30	
Continuous drain current ($T_J = 150$ °C) ^e	V_{GS} at 10 V	14	A
		9	
Pulsed drain current ^a	I_{DM}	96	
Linear derating factor		0.28	W/°C
Single pulse avalanche energy ^b	E_{AS}	226	mJ
Maximum power dissipation	P_D	35	W
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	$T_J = 125$ °C	100	V/ns
Reverse diode dv/dt ^d	dv/dt	10	
Soldering recommendations (peak temperature) ^c	For 10 s	260	°C
Mounting torque, M3 screw		0.6	Nm

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 120$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω, $I_{AS} = 4.0$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $di/dt = 100$ A/μs, starting $T_J = 25$ °C
- Limited by maximum junction temperature

THERMAL RESISTANCE RATINGS

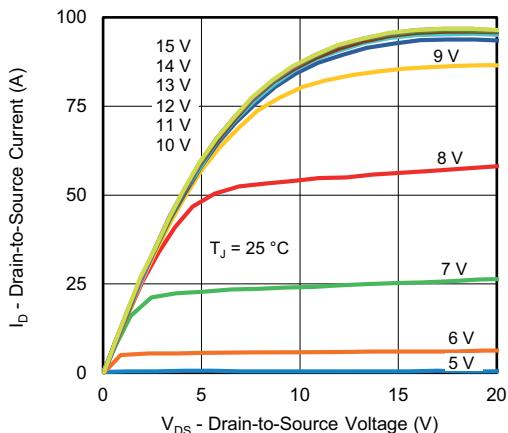
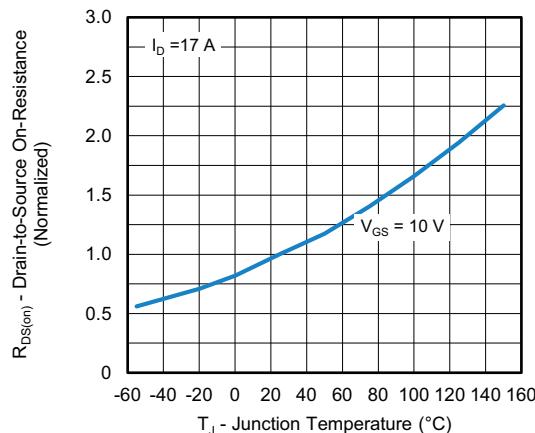
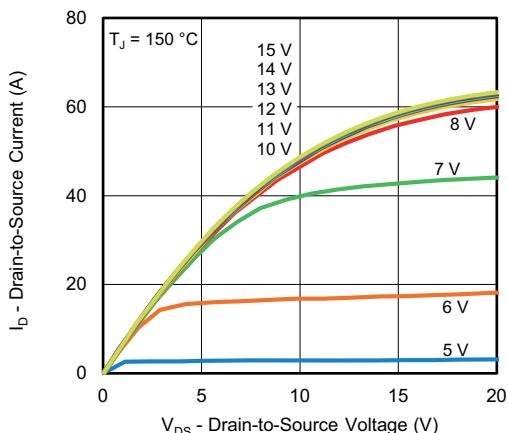
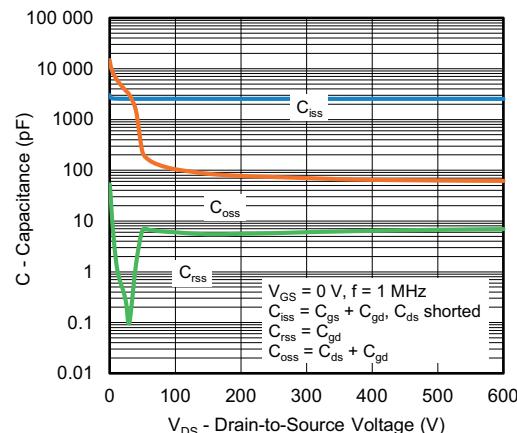
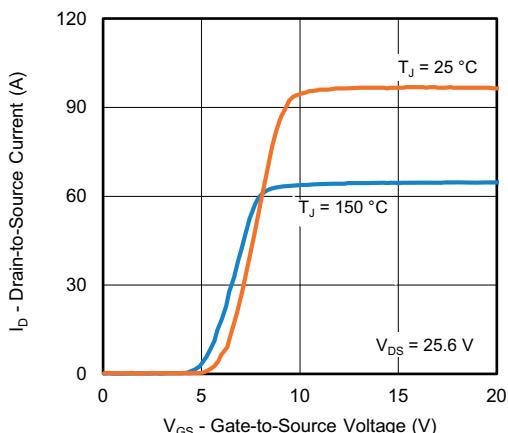
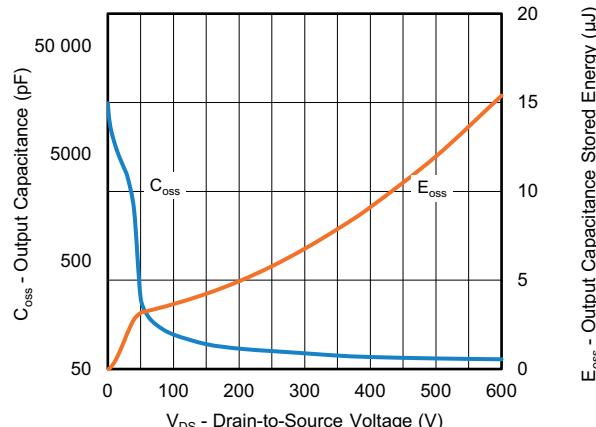
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	65	
Maximum junction-to-case (drain)	R_{thJC}	-	3.6	°C/W

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μA		600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1$ mA		-	0.64	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μA		3.0	-	5.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20$ V		-	-	± 100	nA
		$V_{GS} = \pm 30$ V		-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600$ V, $V_{GS} = 0$ V		-	-	1	
		$V_{DS} = 480$ V, $V_{GS} = 0$ V, $T_J = 125$ °C		-	-	10	μA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10$ V	$I_D = 17$ A	-	0.070	0.080	Ω
Forward transconductance ^a	g_{fs}	$V_{DS} = 20$ V, $I_D = 17$ A		-	4.6	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0$ V, $V_{DS} = 100$ V, $f = 1$ MHz		-	2557	-	pF
Output capacitance	C_{oss}			-	105	-	
Reverse transfer capacitance	C_{rss}			-	6	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{DS} = 0$ V to 480 V, $V_{GS} = 0$ V		-	79	-	
Effective output capacitance, time related ^b	$C_{o(tr)}$			-	499	-	
Total gate charge	Q_g		$V_{GS} = 10$ V	$I_D = 17$ A, $V_{DS} = 480$ V	-	42	63
Gate-source charge	Q_{gs}				-	19	-
Gate-drain charge	Q_{gd}				-	10	-
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 480$ V, $I_D = 17$ A, $V_{GS} = 10$ V, $R_g = 9.1$ Ω		-	31	62	ns
Rise time	t_r			-	96	144	
Turn-off delay time	$t_{d(off)}$			-	37	74	
Fall time	t_f			-	31	62	
Gate input resistance	R_g	$f = 1$ MHz, open drain		0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	35	A
Pulsed diode forward current	I_{SM}			-	-	96	
Diode forward voltage	V_{SD}	$T_J = 25$ °C, $I_S = 17$ A, $V_{GS} = 0$ V		-	-	1.2	V
Reverse recovery time	t_{rr}	$T_J = 25$ °C, $I_F = I_S = 17$ A, $di/dt = 80$ A/μs, $V_R = 25$ V		-	441	882	ns
Reverse recovery charge	Q_{rr}			-	5.2	10.4	μC
Reverse recovery current	I_{RRM}			-	21	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

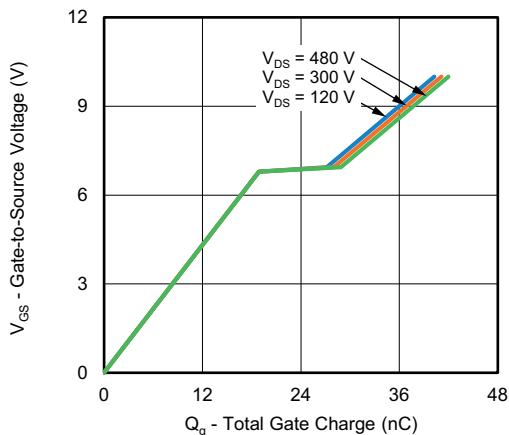


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

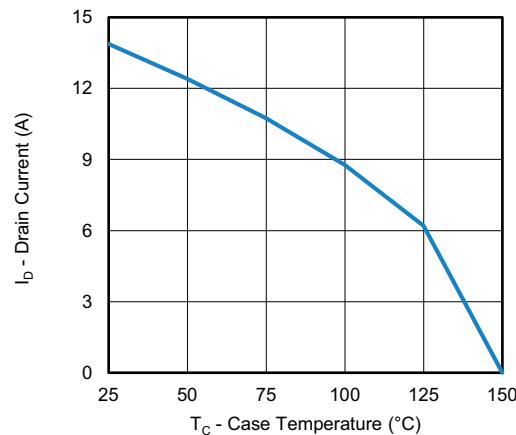


Fig. 10 - Maximum Drain Current vs. Case Temperature

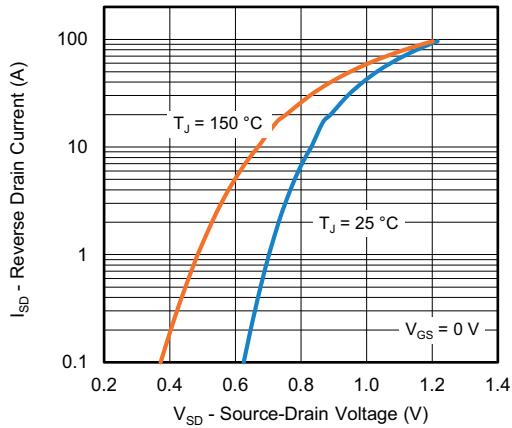


Fig. 8 - Typical Source-Drain Diode Forward Voltage

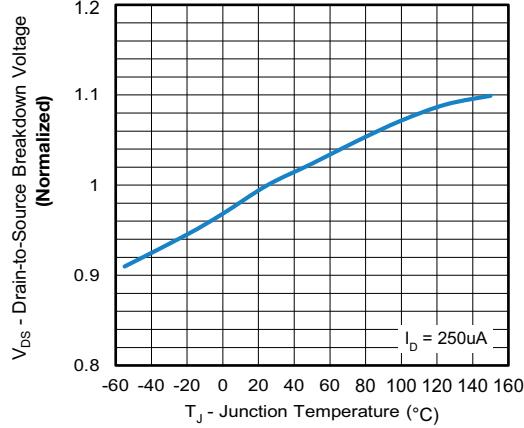


Fig. 11 - Temperature vs. Drain-to-Source Voltage

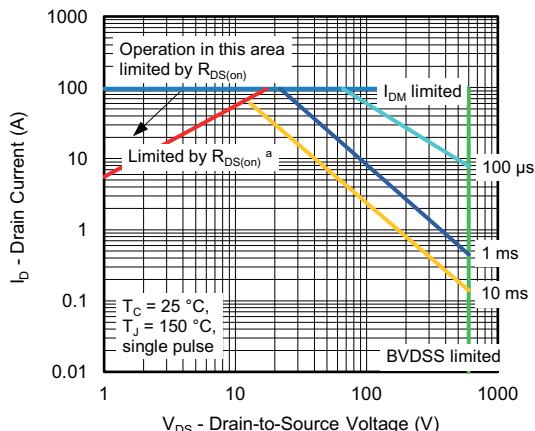


Fig. 9 - Maximum Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

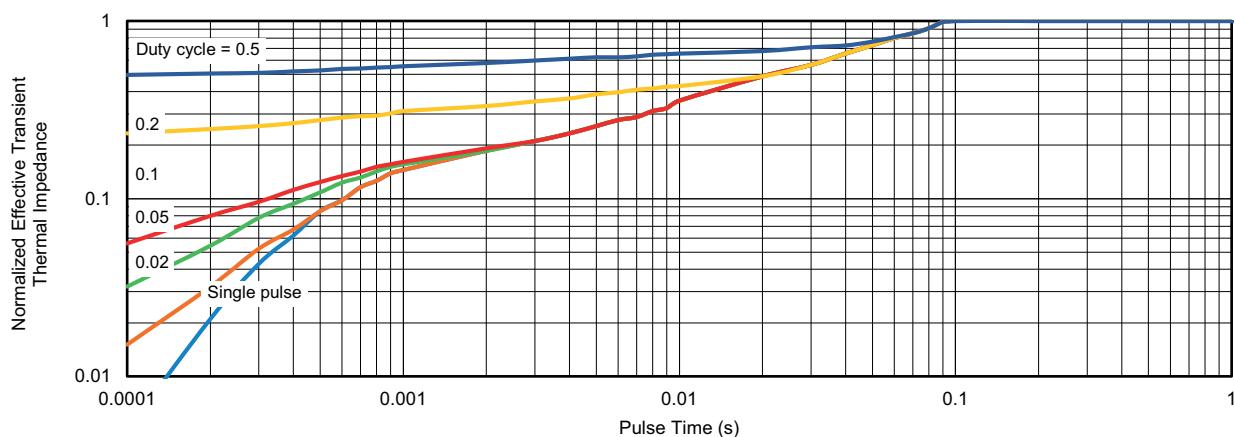


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

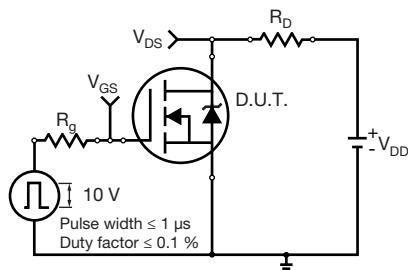


Fig. 13 - Switching Time Test Circuit

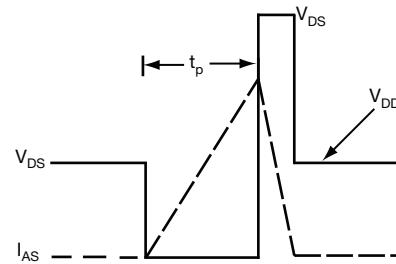


Fig. 16 - Unclamped Inductive Waveforms

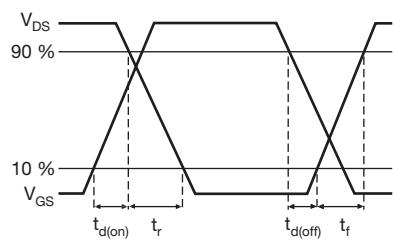


Fig. 14 - Switching Time Waveforms

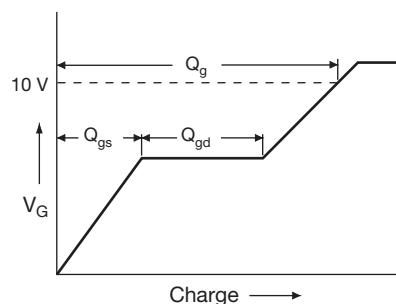


Fig. 17 - Basic Gate Charge Waveform

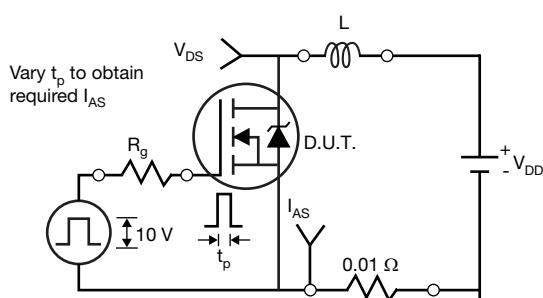


Fig. 15 - Unclamped Inductive Test Circuit

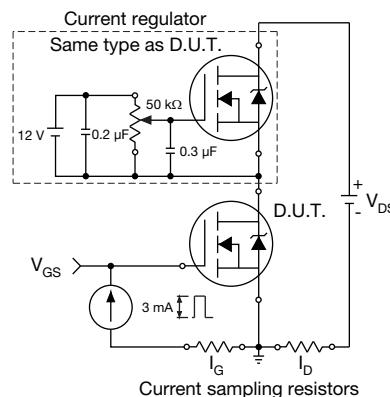


Fig. 18 - Gate Charge Test Circuit

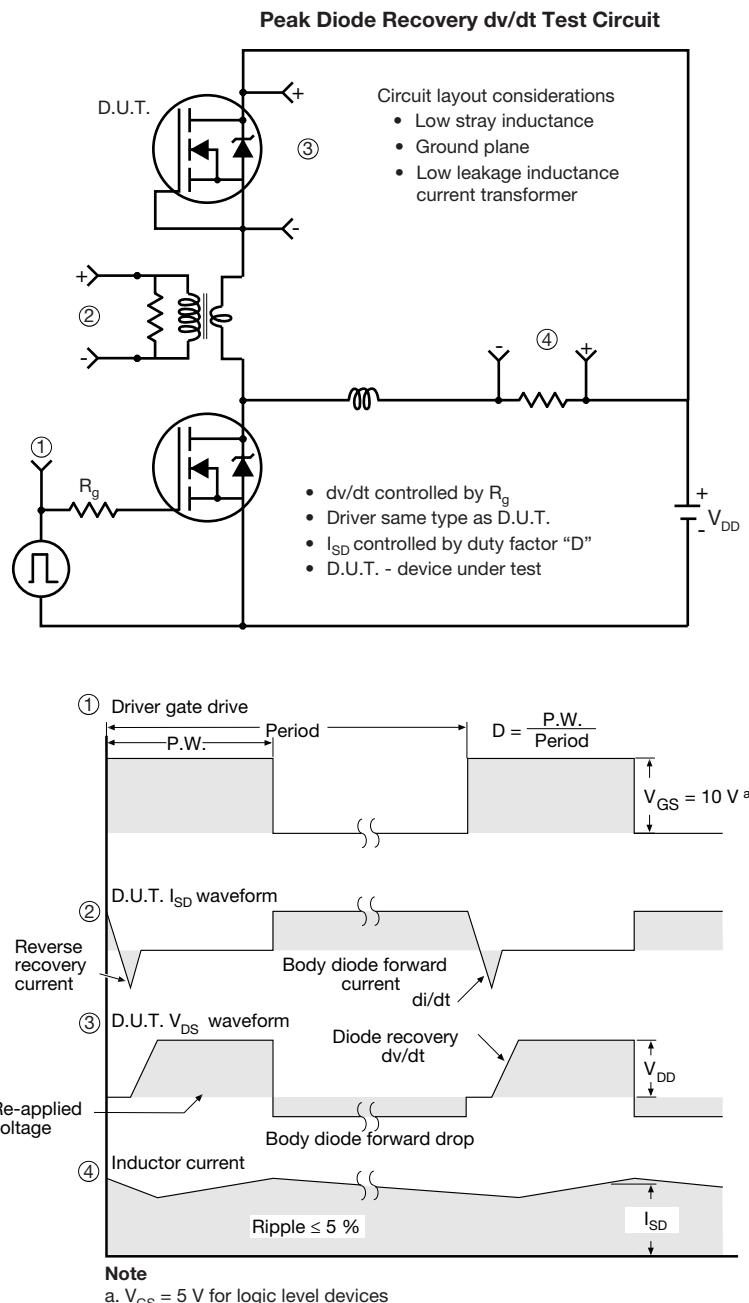


Fig. 19 - For N-Channel

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